

Supplementary Data

“Dragging mode” Electrohydrodynamic Jet Printing of Polymer-Wrapped Semiconducting Single-Walled Carbon Nanotube for NO Gas-Sensing Field-Effect Transistors

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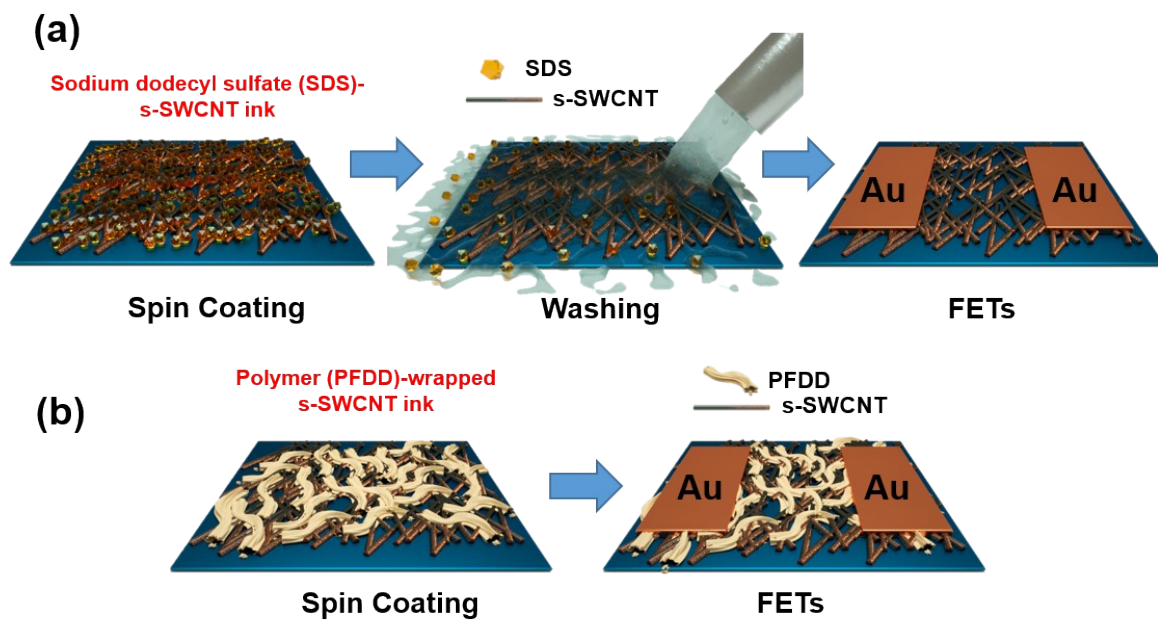


Figure S1. (a) The production process of non-polymer wrapping SDS-s-SWCNTs. (b) The production process of polymer wrapping PFDD-s-SWCNTs.

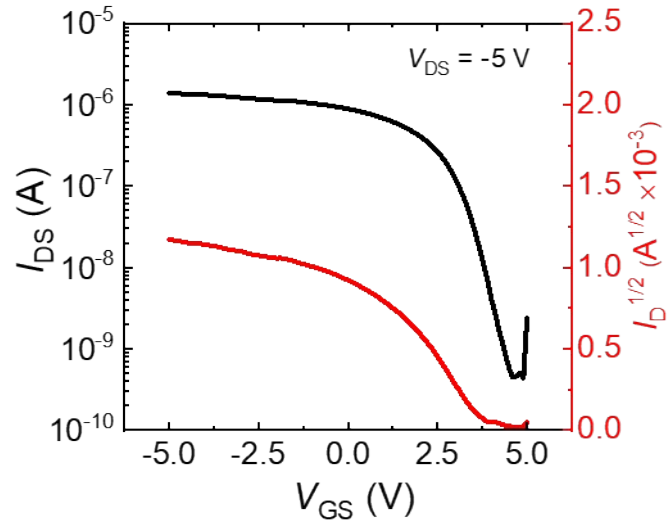


Figure S2. Transfer characteristics of the FETs for SDS-s-SWCNT.

Table S1. Electrical characteristics of the SDS-s-SWCNTs FETs depending on the spin coating.

Spin Coating	μ_{FET} ($\text{cm}^2/(\text{V}\cdot\text{s})$)	V_{th} (V)	$I_{\text{on}}/I_{\text{off}}$	SS (V/dec)
SDS-s-SWCNT	2.78 ± 0.03	4.16	3.12×10^3	0.614

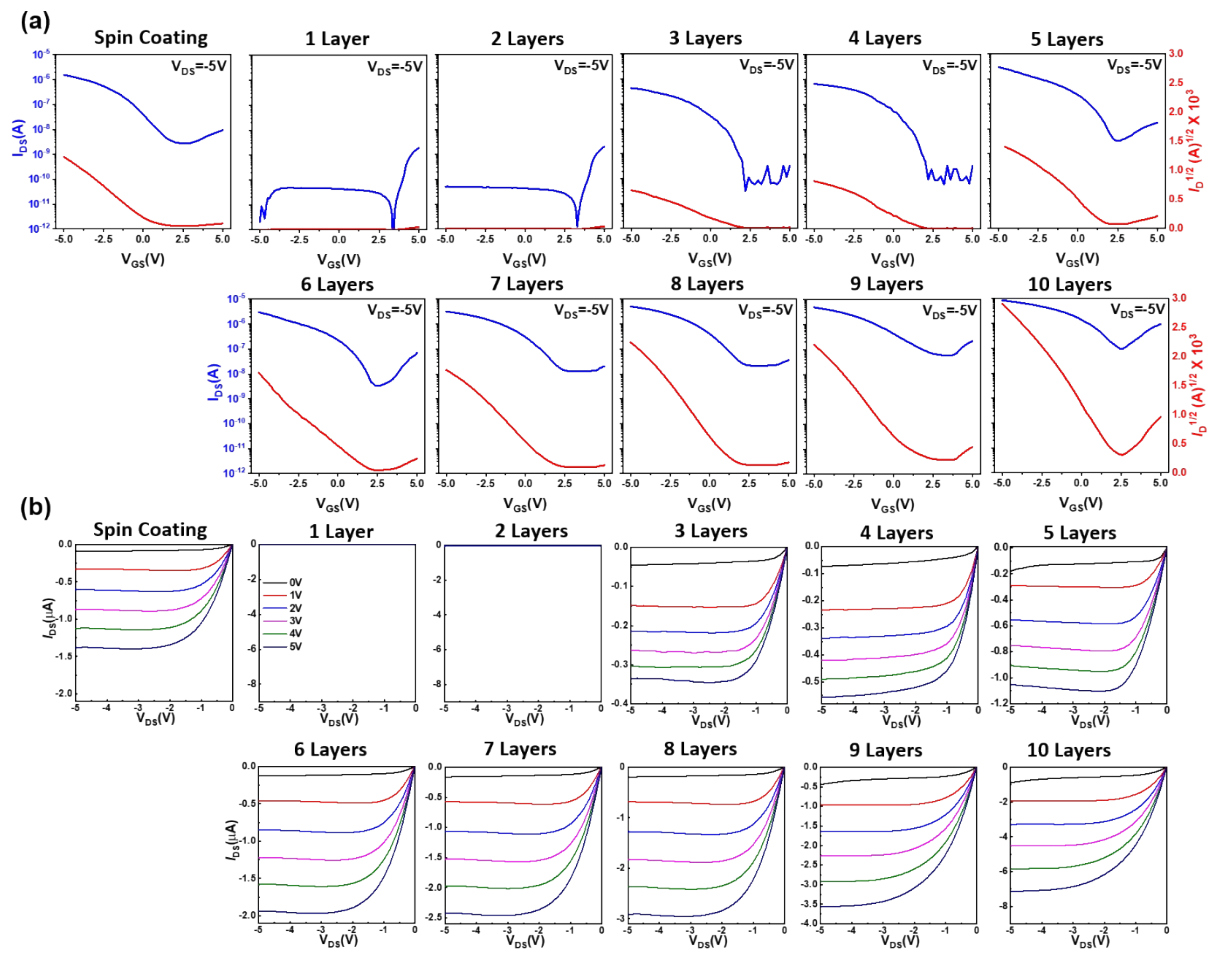


Figure S3. (a) Transfer and (b) Output characteristics of the PFDD-s-SWCNTs FETs depending on the number of layers.

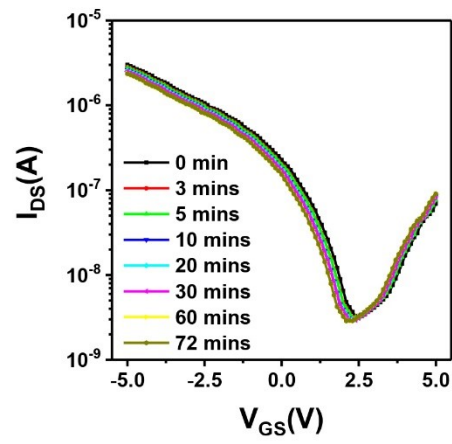


Figure S4. Transfer characteristics of the PFDD-*s*-SWCNTs FETs according to the sustained gate-bias stress ($V_G = -5$ V) for 72 min. The number of layers of the PFDD-*s*-SWCNTs is six.